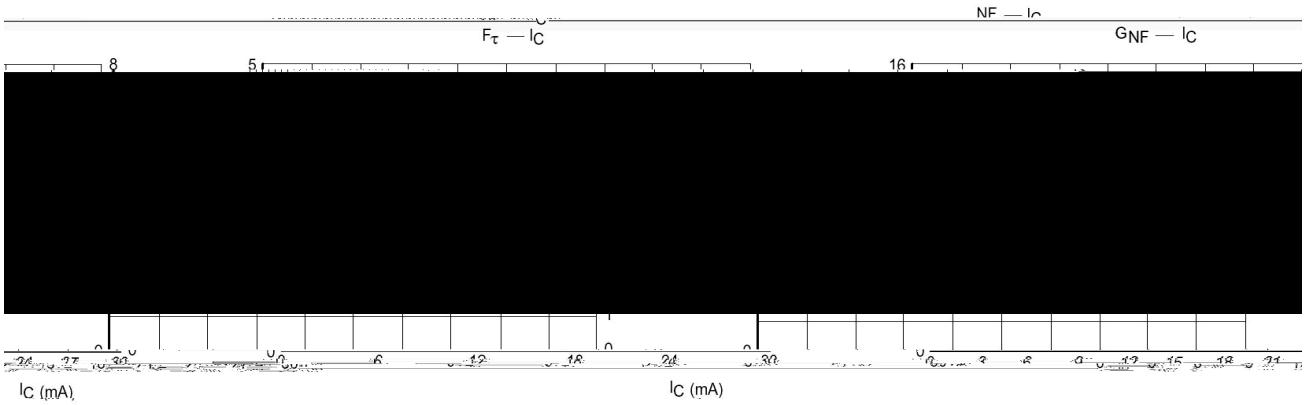
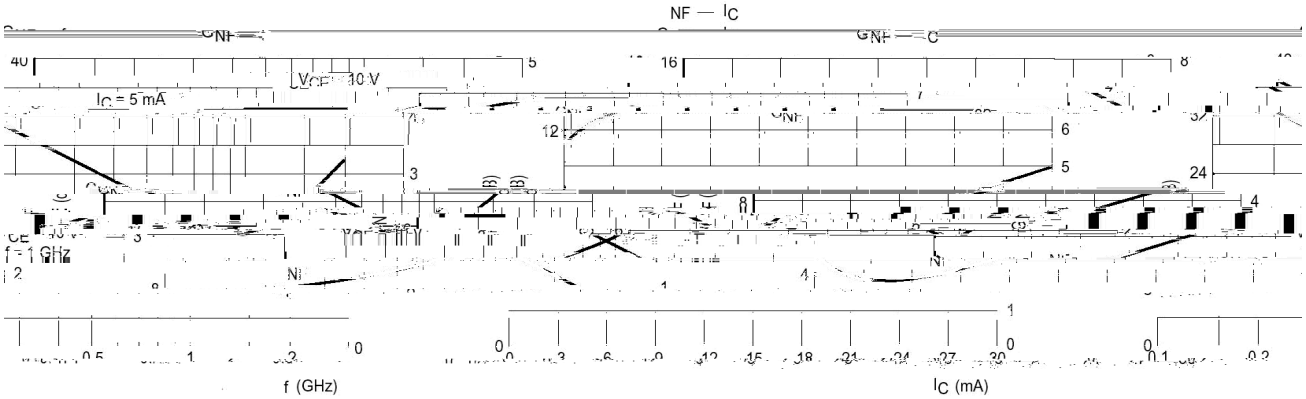
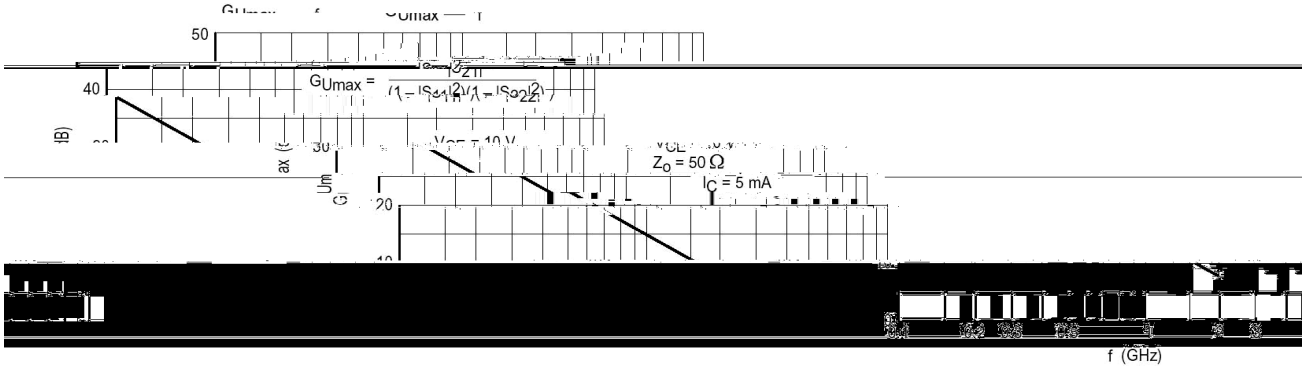
SOT-23	NPN	Silicon NPN transistor in a SOT-23 Plastic Package.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	25	V
Collector to Emitter Voltage	V_{CEO}	15	V
Emitter to Base Voltage	V_{EBO}	2	V
Collector Current	I_C	30	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	150	
Storage Temperature Range			

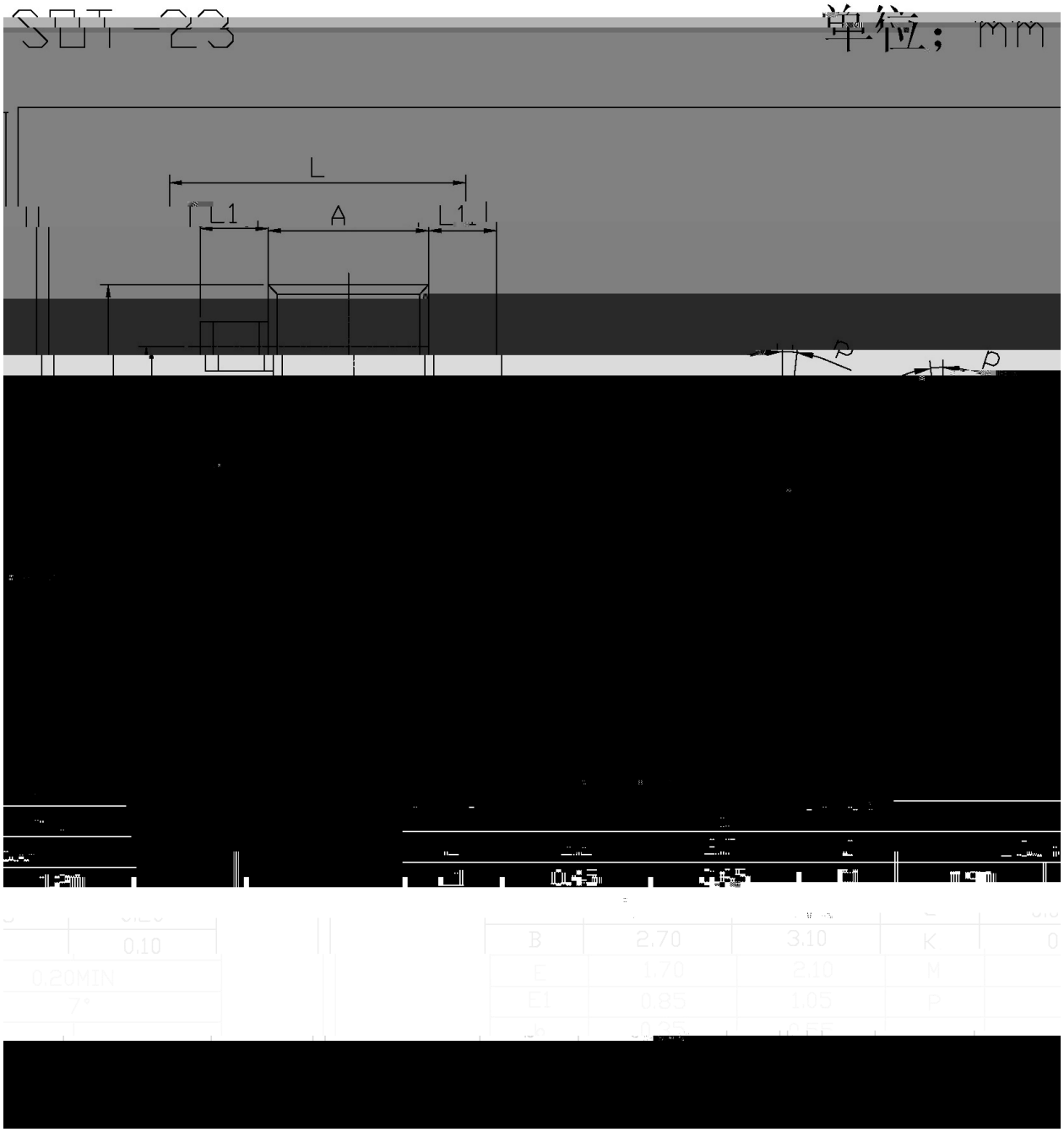
/ Electrical Characteristic Curve



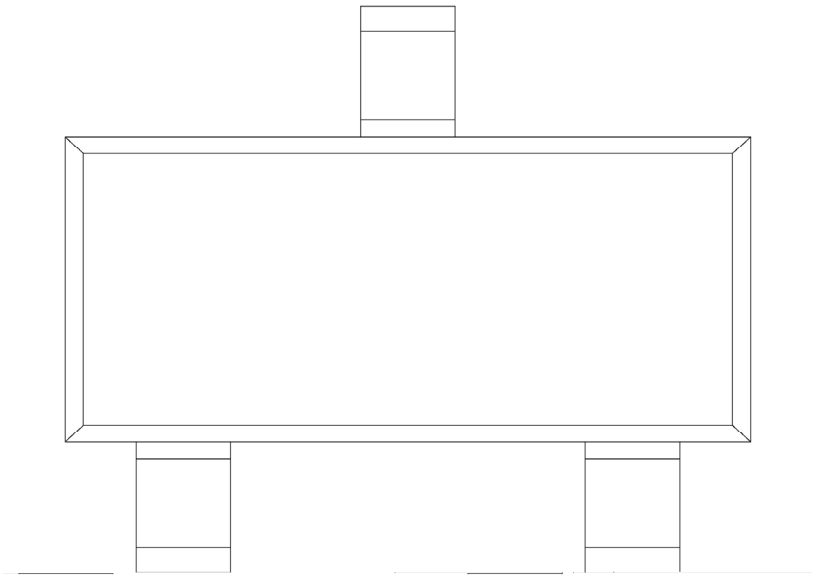




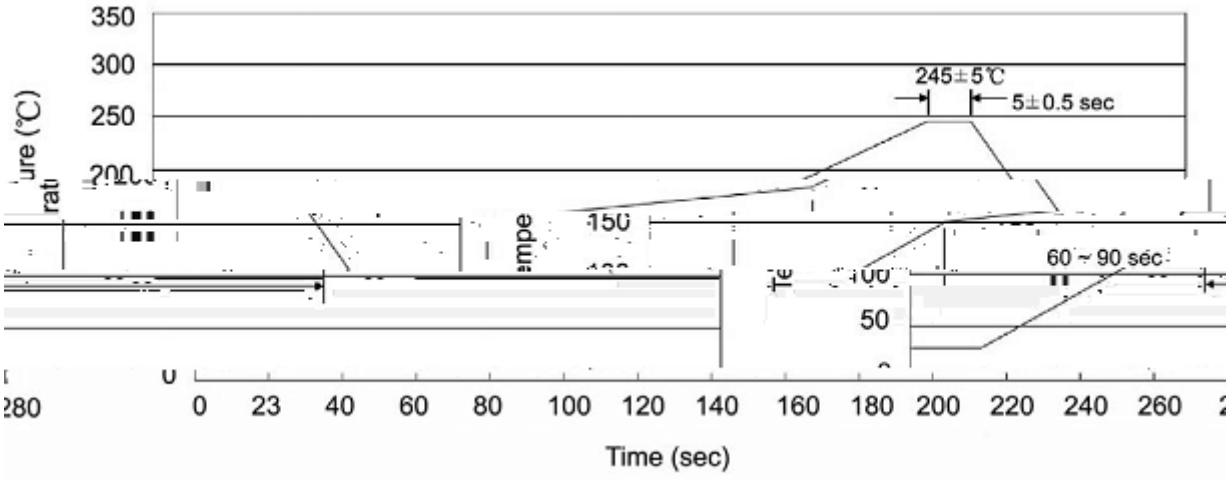
/ Package Dimensions



/ Marking Instructions



( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

1	25	150	60	90sec;	1.Preheating:25~150 , Time:60~90sec.
2	245±5			5±0.5sec;	2.Peak Temp.:245±5 , Duration:5±0.5sec.
3		2	10	/sec.	3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260±5	10±1 sec.	Temp.:260±5	Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-23	3,000	10	30,000	6	180,000	7 ×8	180×120×180	390×385×205